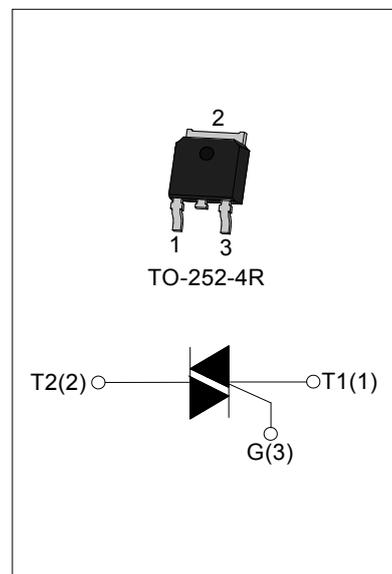




DESCRIPTION:

With high ability to withstand the shock loading of large current, JST06 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, the products especially recommended for use on inductive load. Package TO-252-4R is RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	600/800	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	°C
Operating junction temperature range		T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600/800	V
RMS on-state current	TO-252-4R ($T_C=100^\circ\text{C}$)	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	60	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	18	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	I - II - III	di/dt	50	$\text{A}/\mu\text{s}$
	IV		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				C	B	
I_{GT}	$V_D=12\text{V } R_L=30\Omega$	I - II -III	MAX	25	50	mA
		IV		50	70	
V_{GT}		ALL	MAX	1.5		V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I -III-IV	MAX	50	70	mA
		II		60	80	
I_H	$I_{TM}=0.2\text{A}$		MAX	40	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	200	500	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=8.5\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	1	mA

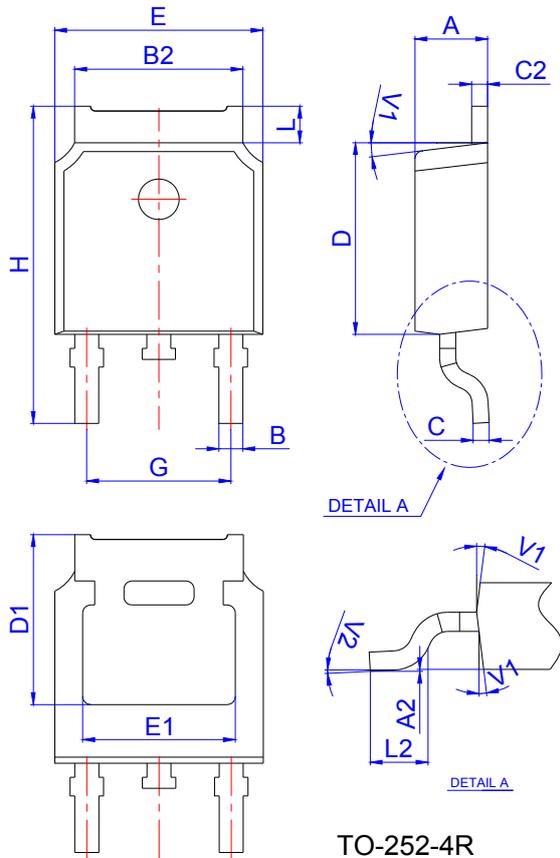
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252-4R	2.7	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	junction to ambient		70	

ORDERING INFORMATION

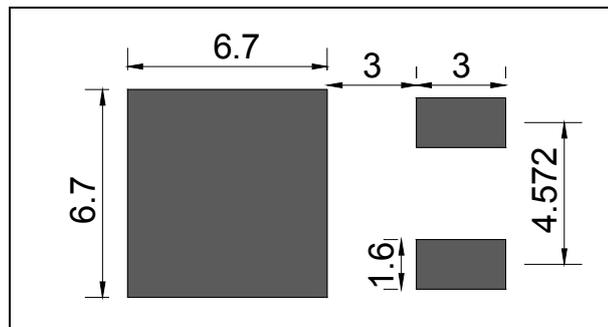
JieJie Microelectronics Co.,Ltd	J Triacs $I_{T(RMS)}:6\text{A}$	ST K:TO-252-4R KTR:TO-252-4R(Tape&Reel)	06	K	-600 600: DRM / RRM 600 : DRM / RRM \geq 800V	C C: $I_{GT1-3}\leq 25\text{mA } I_{GT4}\leq 50\text{mA}$ B: $I_{GT1-3}\leq 50\text{mA } I_{GT4}\leq 70\text{mA}$
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PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

FOOTPRINT-TO-252-4R (dimensions in mm)



PACKAGE INFORMATION

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-252-4R	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252-4R	TAPING	2,500	25,000	13 inch

FIG.1: Maximum power dissipation versus RMS on-state current

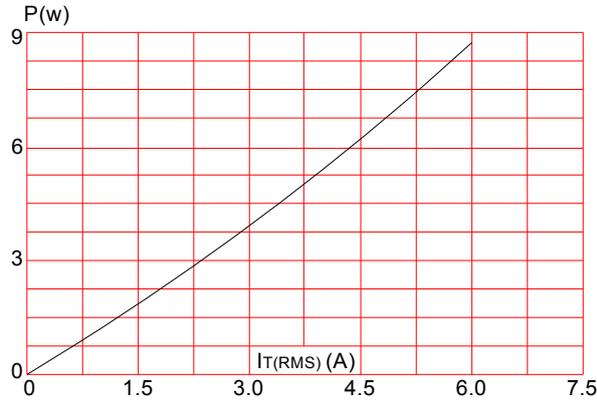


FIG.3: Surge peak on-state current versus number of cycles

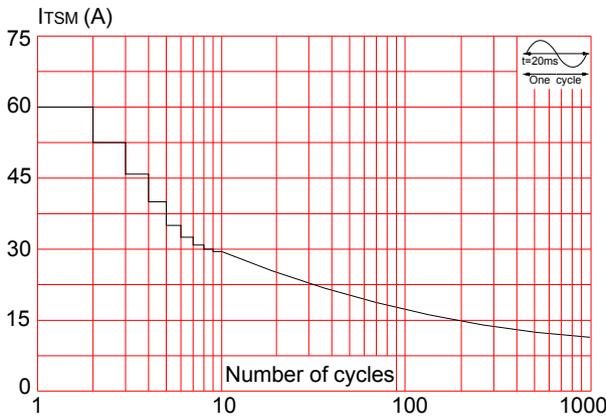


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II -III: $dI/dt < 50\text{A}/\mu\text{s}$; IV: $dI/dt < 10\text{A}/\mu\text{s}$)

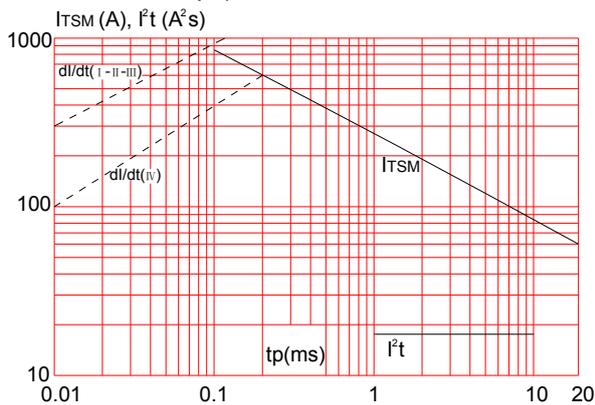


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: $35\mu\text{m}$) (full cycle)

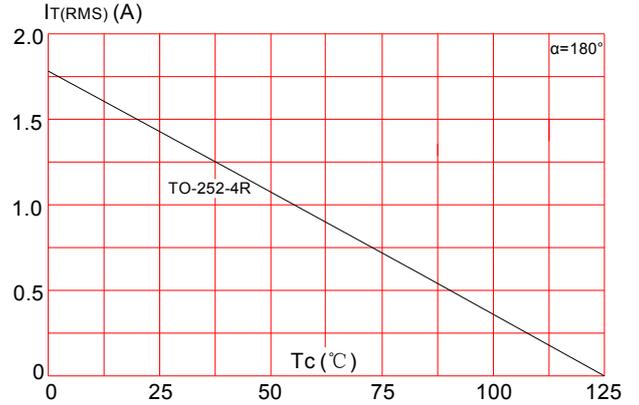


FIG.4: On-state characteristics (maximum values)

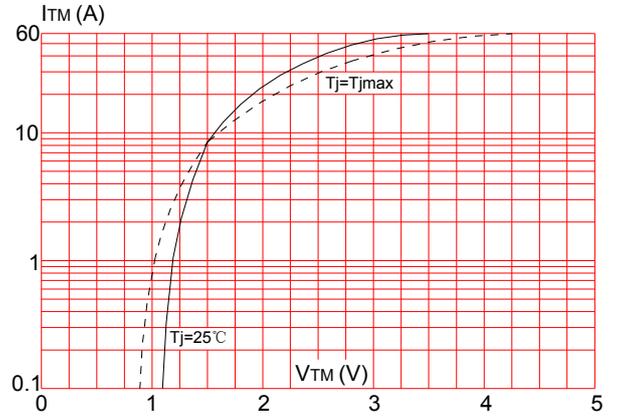


FIG.6: Relative variations of gate trigger current versus junction temperature

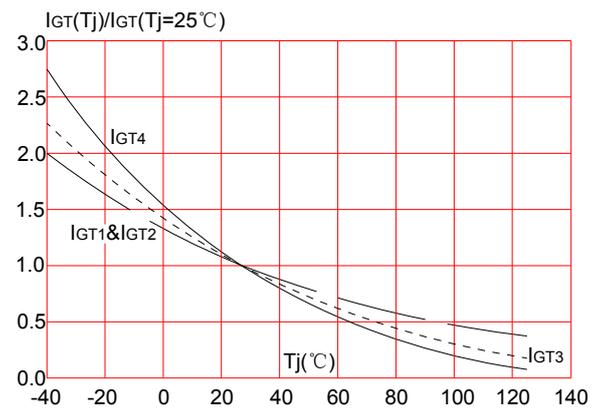


FIG.7: Relative variations of holding current versus junction temperature

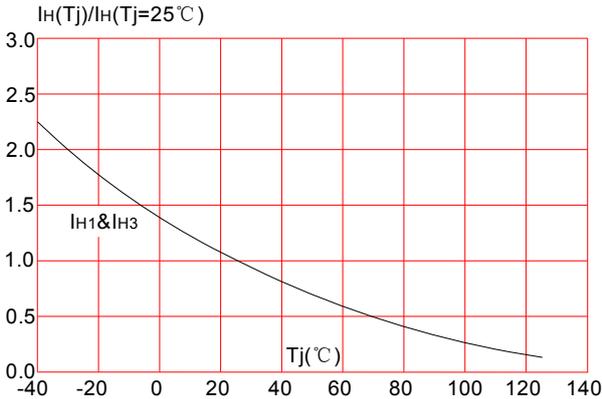
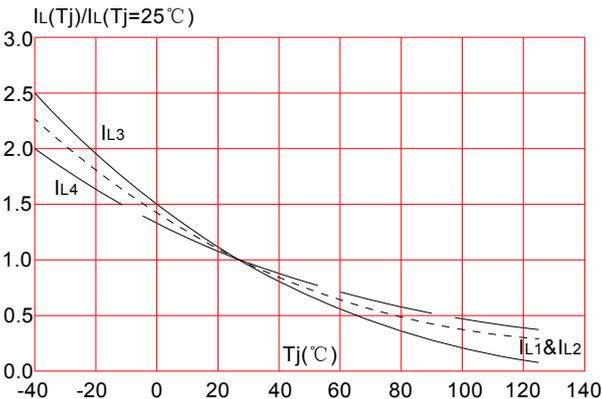
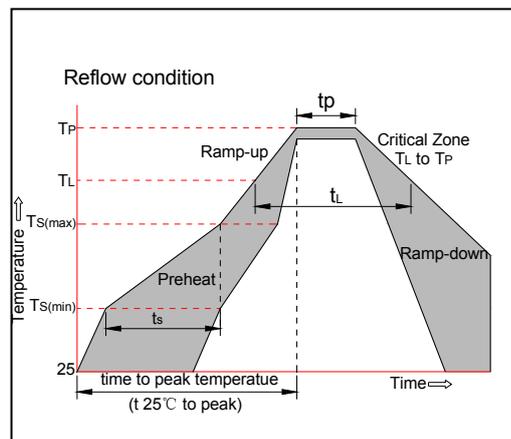


FIG.8: Relative variations of latching current versus junction temperature



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



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